

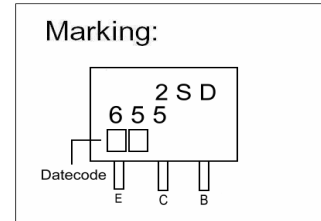
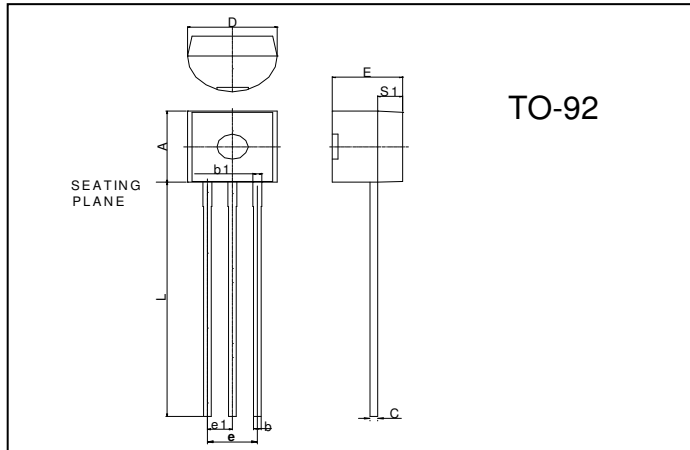
## G2SD655

Silicon NPN Epitaxial

### Application

Low frequency power amplifier, Muting.

### Package Dimensions



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.45	4.7	D	4.44	4.7
S1	1.02	-	E	3.30	3.81
b	0.36	0.51	L	12.70	-
b1	0.36	0.76	e1	1.150	1.390
C	0.36	0.51	e	2.42	2.66

### Absolute Maximum Ratings (Ta = 25°C)

Parameter		Ratings	Unit
Collector to Base Voltage	V <sub>CBO</sub>	30	V
Collector to Emitter Voltage	V <sub>CEO</sub>	15	V
Emitter to Base Voltage	V <sub>EBO</sub>	5	V
Collect Current(DC)	I <sub>C</sub>	0.7	A
Collect peak current	I <sub>C(peak)</sub>	1.0	A
Junction Temperature	T <sub>J</sub>	+150	°C
Storage Temperature Range	T <sub>stg</sub>	-55 ~ +150	°C
Total Power Dissipation	P <sub>D</sub>	500	mW

### Electrical Characteristics (Ta = 25°C)

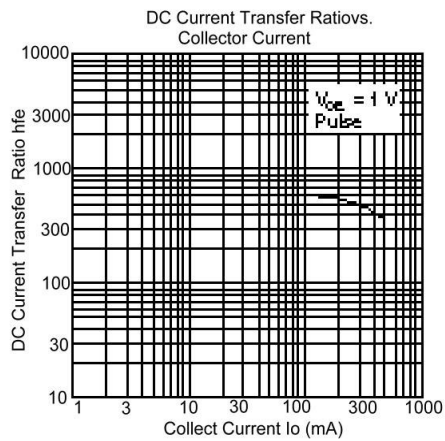
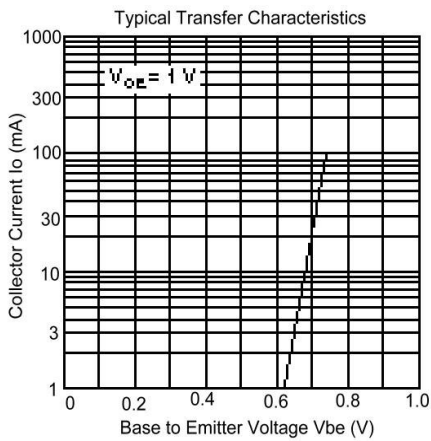
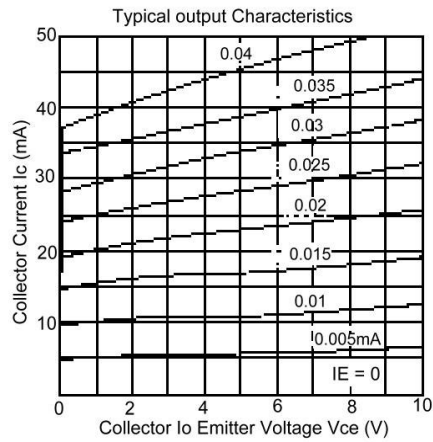
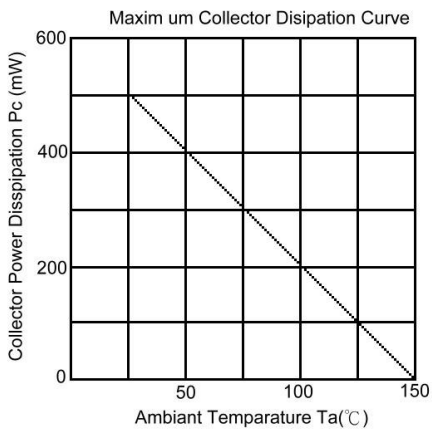
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
V <sub>CBO</sub>	30	-	-	V	I <sub>C</sub> =10uA, I <sub>E</sub> =0
V <sub>CEO</sub>	15	-	-	V	I <sub>C</sub> =1mA, R <sub>BE</sub> =∞
V <sub>EBO</sub>	5	-	-	V	I <sub>E</sub> =10uA, I <sub>C</sub> =0
I <sub>CBO</sub>	-	-	1.0	uA	V <sub>CB</sub> =20V, I <sub>E</sub> =0
V <sub>BE</sub>	-	-	1.0	V	V <sub>CE</sub> =1V, I <sub>C</sub> =150mA
V <sub>CE(sat)</sub>	-	0.15	0.5	V	I <sub>C</sub> =500mA, I <sub>B</sub> =50mA *2
h <sub>FE1</sub> *1	250	-	1200		V <sub>CE</sub> =1V, I <sub>C</sub> =150mA *2
f <sub>T</sub>	-	250	-	MHz	V <sub>CE</sub> =1V, I <sub>C</sub> =150mA

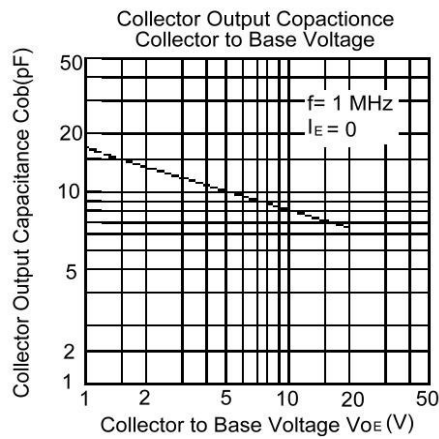
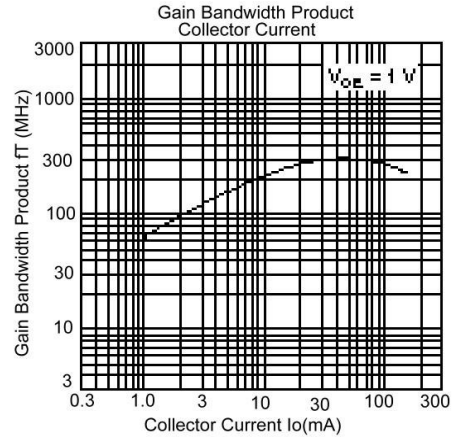
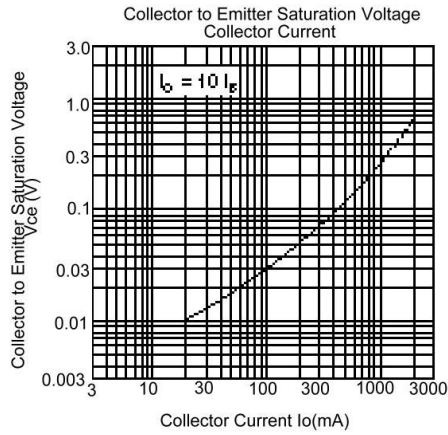
Notes: 1. The G2SD655 is grouped by hFE as follows.  
2. Pulse test

### Classification of Rank

Rank	D	E	F
Range	250-500	400-800	600-1200

## Characteristics Curve





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